Abstracts

Extraction of parasitic parameters of dummy devices on different silicon substrates (1998 Vol. III [MWSYM])

L.P. Chen, Y.P. Ho, D.C. Lin, B.M. Tseng, H.Y. Lee, R.F. Guan, G.W. Huang, Y.C. Chen, W.Y. Wen and C.L. Chen. "Extraction of parasitic parameters of dummy devices on different silicon substrates (1998 Vol. III [MWSYM])." 1998 MTT-S International Microwave Symposium Digest 98.3 (1998 Vol. III [MWSYM]): 1863-1866.

S-parameters of dummy devices fabricated on Si substrates with different resistivities are measured and analyzed to study the effects of substrate resistivity on the microwave characteristics. An equivalent parasitic circuit model is proposed and the extraction procedure also developed. The substrate resistivity effects can be explained well by the proposed model.

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